Serial Number: 10/053,300 Filing Date: January 17, 2002

Title: TRANSISTOR STRUCTURE HAVING SEDUCED SANSISTOR LEAKAGE ATTRIBUTES

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<u>S/N 10/053,300</u> <u>PATENT</u>

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Vishnu K. Agarwal et al.

Examiner: Hoai V. Pham

Serial No.:

10/053,300

Group Art Unit: 2814

Filed:

January 17, 2002

Docket: 303.780US1

Title:

TRANSISTOR STRUCTURE HAVING REDUCED TRANSISTOR LEAKAGE

**ATTRIBUTES** 

## AMENDMENT UNDER 37 C.F.R. § 1.312

Mail Stop Issue Fee Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In response to the Notice of Allowance and Notice of Allowability mailed March 17, 2006, please amend as follows: